

Fast switching diode chip in EMCON 3-Technology

FEATURES:

- 600V EMCON 3 technology 70 µm chip
- soft, fast switching
- low reverse recovery charge
- small temperature coefficient

This chip is used for:

- power module
- discrete components



Applications:

- drives
- white goods
- resonant applications

Chip Type	V_R	I _F	Die Size	Package
SIDC05D60C6	600V	15A	2.37 x 1.9 mm ²	sawn on foil

MECHANICAL PARAMETER:

Raster size	2.37 x 1.9		
Area total / active	4.5 / 2.88	mm ²	
Anode pad size	1.95 x 1.48		
Thickness	70	μm	
Wafer size	150	mm	
Flat position	180	deg	
Max. possible chips per wafer	3276 pcs		
Passivation frontside			
Anode metallization	3200 nm AlSiCu		
Cathode metallization	Ni Ag –system suitable for epoxy and soft solder die bonding		
Die bond	electrically conductive glue or solder		
Wire bond	AI, ≤500μm		
Reject ink dot size	Ø 0.65mm; max 1.2mm		
Recommended storage environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C		

Edited by INFINEON Technologies, AIM PMD D CID CLS, L4531M, Edition 1.1, 10.07.2006



Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}		600	V
Continuous forward current limited by	1_		1)	- A
T _{jmax}	I _F			
Maximum repetitive forward current	1		30	
limited by T _{jmax}	/ FRM		30	
Operating junction and storage temperature	$T_{\rm j}$, $T_{ m stg}$		-40+175	°C

¹⁾ depending on thermal properties of assembly

Static Electrical Characteristics (tested on chip), T_i =25 °C, unless otherwise specified

Parameter	Symbol	Cond	Value			Unit	
raiailletei	Syllibol	Cona	itions	min.	nin. Typ. max.		l Ollit
Reverse leakage current	I_{R}	V _R =600V	<i>T_j</i> =25 °C			27	μΑ
Cathode-Anode breakdown Voltage	V _{Br}	I _R =0.25mA	<i>T_j</i> =25°C	600			V
Forward voltage drop	V_{F}	I _F =15A	<i>T_j</i> =25 °C	1.25	1.6	1.95	V

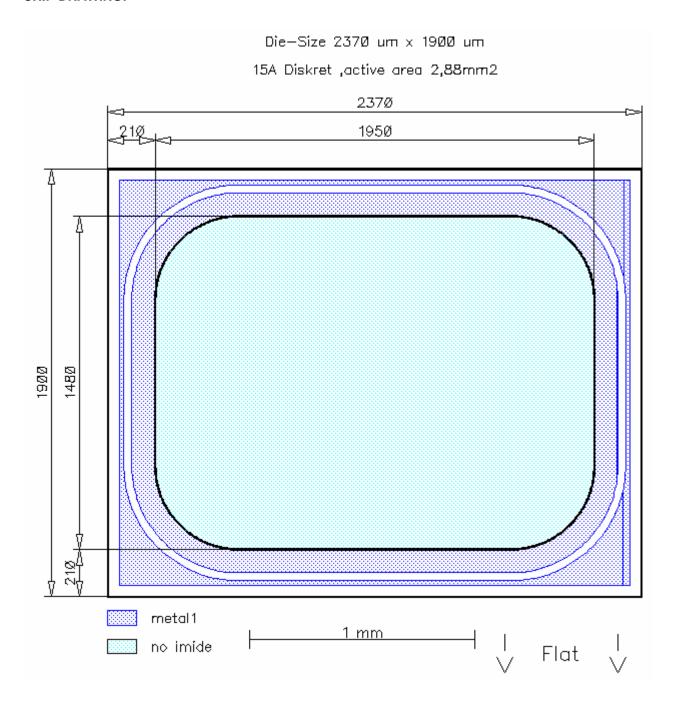
Dynamic Electrical Characteristics (verified by design/characterization), inductive load

Parameter	Symbol	Conditions		Value 2)			Unit
raiailletei	Syllibol	Condi	min.	Тур.	max.		
Peak reverse recovery current	I _{RM}	$I_F=15A$ di/dt=1600A/ms $V_R=300V$ $V_{GE}=-15V$	$T_j = 25 \text{ °C}$ $T_j = 125 \text{ °C}$ $T_j = 150 \text{ °C}$		23.0 25.0 26.0		A
Recovered charge	Q _r	$I_F=15A$ di/dt=1600A/ms $V_R=300V$ $V_{GE}=-15V$	$T_j = 25 \text{ °C}$ $T_j = 125 \text{ °C}$ $T_j = 150 \text{ °C}$		0.80 1.40 1.70		μC
Reverse recovery energy	E _{rec}	$I_F=15A$ di/dt=1600A/ms $V_R=300V$ $V_{GE}=-15V$	$T_j = 25 ^{\circ}\text{C}$ $T_j = 125 ^{\circ}\text{C}$ $T_j = 150 ^{\circ}\text{C}$		0.16 0.28 0.37		mJ

²⁾ values also influenced by parasitic L- and C- in measurement and package.



CHIP DRAWING:





This chip data sheet refers to the device data sheet Description: AQL 0,65 for visual inspection according to failure catalog Electrostatic Discharge Sensitive Device according to MIL-STD 883 Test-Normen Villach/Prüffeld

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